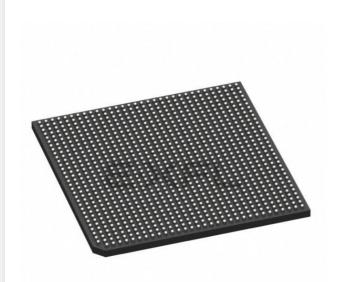
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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	1023-BFBGA, FCBGA
Supplier Device Package	1023-FCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8572evtaule

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Overview

- Supports fully nested interrupt delivery
- Interrupts can be routed to external pin for external processing.
- Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
- Interrupt summary registers allow fast identification of interrupt source.
- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, SSL/TLS, SRTP, 802.16e, and 3GPP
 - Four crypto-channels, each supporting multi-command descriptor chains
 - Dynamic assignment of crypto-execution units through an integrated controller
 - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
 - PKEU—public key execution unit
 - RSA and Diffie-Hellman; programmable field size up to 4096 bits
 - Elliptic curve cryptography with F₂m and F(p) modes and programmable field size up to 1023 bits
 - DEU—Data Encryption Standard execution unit
 - DES, 3DES
 - Two key (K1, K2, K1) or three key (K1, K2, K3)
 - ECB, CBC and OFB-64 modes for both DES and 3DES
 - AESU—Advanced Encryption Standard unit
 - Implements the Rijndael symmetric key cipher
 - ECB, CBC, CTR, CCM, GCM, CMAC, OFB-128, CFB-128, and LRW modes
 - 128-, 192-, and 256-bit key lengths
 - AFEU—ARC four execution unit
 - Implements a stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
 - MDEU—message digest execution unit
 - SHA-1 with 160-bit message digest
 - SHA-2 (SHA-256, SHA-384, SHA-512)
 - MD5 with 128-bit message digest
 - HMAC with all algorithms
 - KEU—Kasumi execution unit
 - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
 - Also supports A5/3 and GEA-3 algorithms
 - RNG—random number generator
 - XOR engine for parity checking in RAID storage applications
 - CRC execution unit
 - CRC-32 and CRC-32C
- Pattern Matching Engine with DEFLATE decompression



Overview

- Ability to launch DMA from single write transaction
- Serial RapidIO interface unit
 - Supports RapidIO Interconnect Specification, Revision 1.2
 - Both 1x and 4x LP-serial link interfaces
 - Long- and short-haul electricals with selectable pre-compensation
 - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
 - Auto-detection of 1x- and 4x-mode operation during port initialization
 - Link initialization and synchronization
 - Large and small size transport information field support selectable at initialization time
 - 34-bit addressing
 - Up to 256 bytes data payload
 - All transaction flows and priorities
 - Atomic set/clr/inc/dec for read-modify-write operations
 - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
 - Receiver-controlled flow control
 - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
 - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
 - Hardware recovery only
 - Register support is not required for software-mediated error recovery.
 - Accept-all mode of operation for fail-over support
 - Support for RapidIO error injection
 - Internal LP-serial and application interface-level loopback modes
 - Memory and PHY BIST for at-speed production test
- RapidIO–compliant message unit
 - 4 Kbytes of payload per message
 - Up to sixteen 256-byte segments per message
 - Two inbound data message structures within the inbox
 - Capable of receiving three letters at any mailbox
 - Two outbound data message structures within the outbox
 - Capable of sending three letters simultaneously
 - Single segment multicast to up to 32 devIDs
 - Chaining and direct modes in the outbox
 - Single inbound doorbell message structure
 - Facility to accept port-write messages



4 Input Clocks

4.1 System Clock Timing

Table 6 provides the system clock (SYSCLK) AC timing specifications for the MPC8572E.

Table 6. SYSCLK AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Мах	Unit	Notes
SYSCLK frequency	f _{SYSCLK}	33	—	133	MHz	1
SYSCLK cycle time	t _{SYSCLK}	7.5	—	30.3	ns	—
SYSCLK rise and fall time	t _{KH} , t _{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t _{KHK} /t _{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	+/- 150	ps	4, 5, 6

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies.Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," and Section 19.3, "e500 Core PLL Ratio," for ratio settings.

- 2. Rise and fall times for SYSCLK are measured at 0.6 V and 2.7 V.
- 3. Timing is guaranteed by design and characterization.
- 4. This represents the total input jitter—short term and long term—and is guaranteed by design.
- 5. The SYSCLK driver's closed loop jitter bandwidth should be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
- 6. For spread spectrum clocking, guidelines are +0% to -1% down spread at a modulation rate between 20 kHz and 60 kHz on SYSCLK.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.



PLL config input setup time with stable SYSCLK before HRESET negation	100		μs	—
Input setup time for POR configs (other than PLL config) with respect to negation of HRESET	4	_	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of HRESET	2	_	SYSCLKs	1
Maximum valid-to-high imp <u>edance time</u> for actively driven POR configs with respect to negation of HRESET	_	5	SYSCLKs	1

Table 9. RESET Initialization Timing Specifications (continued)

Notes:

2. Reset assertion timing requirements for DDR3 DRAMs may differ.

Table 10 provides the PLL lock times.

Table	10.	PLL	Lock	Times
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Parameter/Condition	Symbol	Min	Typical	Max
PLL lock times	—	100	μs	_
Local bus PLL	—	50	μs	

6 DDR2 and DDR3 SDRAM Controller

This section describes the DC and AC electrical specifications for the DDR2 and DDR3 SDRAM controller interface of the MPC8572E. Note that the required $GV_{DD}(typ)$ voltage is 1.8Vor 1.5 V when interfacing to DDR2 or DDR3 SDRAM, respectively.

6.1 DDR2 and DDR3 SDRAM Interface DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR2 SDRAM.

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
I/O supply voltage	GV _{DD}	1.71	1.89	V	1
I/O reference voltage	MV _{REF} n	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	$MV_{REF}n - 0.04$	$MV_{REF}n + 0.04$	V	3
Input high voltage	V _{IH}	$MV_{REF}n + 0.125$	GV _{DD} + 0.3	V	_
Input low voltage	V _{IL}	-0.3	MV _{REF} n - 0.125	V	_
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.420 V)	I _{ОН}	-13.4	_	mA	—

Table 11	DDR2 SDRAM	Interface DC	Electrical	Characteristics	for GV(tvn)	1 = 18V
		menace DO	Liccultur	onaracteristics		/ I.O V

^{1.} SYSCLK is the primary clock input for the MPC8572E.

DDR2 and DDR3 SDRAM Controller

Table 11. DDR2 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Output low current (V _{OUT} = 0.280 V)	I _{OL}	13.4	_	mA	_

Notes:

1. ${\rm GV}_{\rm DD}$ is expected to be within 50 mV of the DRAM ${\rm GV}_{\rm DD}$ at all times.

- 2. $MV_{REF}n$ is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±2% of the DC value.
- 3. V_{TT} is not applied directly to the device. It is the supply to that far end signal termination is made and is expected to be equal to MV_{REF}*n*. This rail should track variations in the DC level of MV_{REF}*n*.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

Table 12 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR3 SDRAM.

Parameter/Condition	Symbol	Min	Typical	Max	Unit
I/O supply voltage	GV _{DD}	1.425	1.575	V	1
I/O reference voltage	MV _{REF} n	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
Input high voltage	V _{IH}	$MV_{REF}n + 0.100$	GV _{DD}	V	—
Input low voltage	V _{IL}	GND	MV _{REF} <i>n</i> - 0.100	V	—
Output leakage current	I _{OZ}	-50	50	μΑ	3

Notes:

1. ${\rm GV}_{\rm DD}$ is expected to be within 50 mV of the DRAM ${\rm GV}_{\rm DD}$ at all times.

2. $MV_{REF}n$ is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±1% of the DC value.

3. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

Table 13 provides the DDR SDRAM controller interface capacitance for DDR2 and DDR3.

Table 13. DDR2 and DDR3 SDRAM Interface Capacitance for GV_{DD}(typ)=1.8 V and 1.5 V

Parameter/Condition	Symbol	Min	Typical	Мах	Unit
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	_	0.5	pF	1, 2

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V (for DDR2), f = 1 MHz, T_A = 25°C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

2. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25°C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.175 V.

NP

DDR2 and DDR3 SDRAM Controller

Table 18. DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
533 MHz		538	—		
400 MHz		700	—		
MDQS preamble start	t _{DDKHMP}			ns	6
800 MHz		$-0.5 \times t_{MCK} - 0.375$	$\begin{array}{c} -0.5 \times t_{\text{MCK}} \\ +0.375 \end{array}$		
<= 667 MHz		$-0.5\times t_{\text{MCK}}-0.6$	$-0.5 imes t_{MCK}$ +0.6		
MDQS epilogue end	t _{DDKHME}			ns	6
800 MHz		-0.375	0.375		
<= 667 MHz	t _{DDKHME}	-0.6	0.6	ns	6

Note:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)}

(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.

2. All MCK/MCK referenced measurements are made from the crossing of the two signals ±0.1 V.

3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ/MECC/MDM/MDQS.

4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This typically be set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the MPC8572E PowerQUICCTM III Integrated Host Processor Family Reference Manual for a description and understanding of the timing modifications enabled by use of these bits.

 Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.

6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 18, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.



described in Section 21.5, "Connection Recommendations," as long as such termination does not violate the desired POR configuration requirement on these pins, if applicable.

When operating in SGMII mode, the eTSEC EC_GTX_CLK125 clock is not required for this port. Instead, SerDes reference clock is required on SD2_REF_CLK and SD2_REF_CLK pins.

8.3.1 DC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK

The characteristics and DC requirements of the separate SerDes reference clock are described in Section 15, "High-Speed Serial Interfaces (HSSI)."

8.3.2 AC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK

Table 37 lists the SGMII SerDes reference clock AC requirements. Note that SD2_REF_CLK and SD2_REF_CLK are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

Symbol	Parameter Description	Min	Typical	Max	Units	Notes
t _{REF}	REFCLK cycle time	_	10 (8)		ns	1
t _{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles			100	ps	—
t _{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	-50	—	50	ps	—

Table 37. SD2_REF_CLK and SD2_REF_CLK AC Requirements

Note:

1.8 ns applies only when 125 MHz SerDes2 reference clock frequency is selected through cfg_srds_sgmii_refclk during POR.

Ethernet: Enhanced Three-Speed Ethernet (eTSEC)

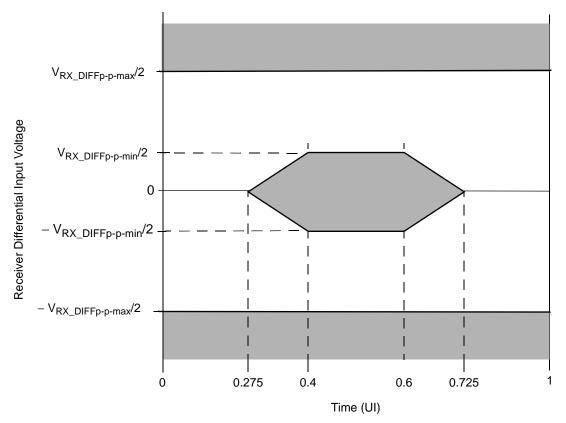


Figure 24. SGMII Receiver Input Compliance Mask

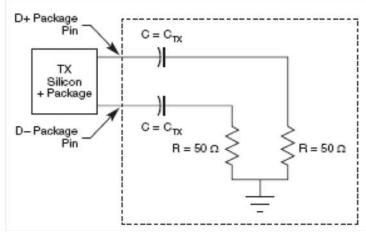


Figure 25. SGMII AC Test/Measurement Load



8.4 eTSEC IEEE Std 1588[™] AC Specifications

Figure 26 shows the data and command output timing diagram.

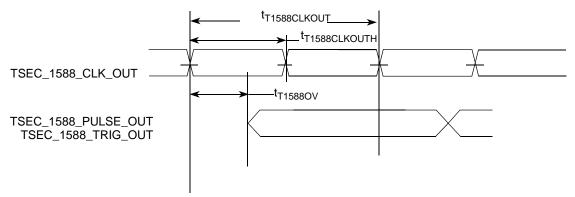


Figure 26. eTSEC IEEE 1588 Output AC Timing

¹ The output delay is count starting rising edge if t_{T1588CLKOUT} is non-inverting. Otherwise, it is count starting falling edge.

Figure 27 shows the data and command input timing diagram.

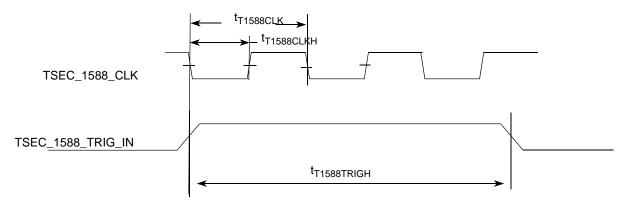




Table 42 provides the IEEE 1588 AC timing specifications.

Table 42. eTSEC IEEE 1588 AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 3.3 V ± 5% or 2.5 V ± 5%

Parameter/Condition	Symbol	Min	Тур	Max	Unit	Note
TSEC_1588_CLK clock period	t _{T1588CLK}	3.3	—	T _{TX_CLK} *9	ns	1
TSEC_1588_CLK duty cycle	t _{T1588} CLKH /t _{T1588} CLK	40	50	60	%	—
TSEC_1588_CLK peak-to-peak jitter	t _{T1588CLKINJ}	—	—	250	ps	—
Rise time eTSEC_1588_CLK (20%-80%)	t _{T1588CLKINR}	1.0	—	2.0	ns	—
Fall time eTSEC_1588_CLK (80%-20%)	t _{T1588CLKINF}	1.0	—	2.0	ns	—
TSEC_1588_CLK_OUT clock period	t _{T1588CLKOUT}	2*t _{T1588CLK}	—	_	ns	—

MPC8572E PowerQUICC III Integrated Processor Hardware Specifications, Rev. 7

NXP Semiconductors



10 Local Bus Controller (eLBC)

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8572E.

10.1 Local Bus DC Electrical Characteristics

Table 46 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 3.3 \text{ V}$ DC.

Parameter	Symbol	Min	Мах	Unit
Supply voltage 3.3V	BV _{DD}	3.13	3.47	V
High-level input voltage	V _{IH}	2	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3 0.8		V
Input current ($BV_{IN}^{1} = 0 V \text{ or } BV_{IN} = BV_{DD}$)	I _{IN}	—	±5	μΑ
High-level output voltage (BV _{DD} = min, I _{OH} = −2 mA)	V _{OH}	BV _{DD} – 0.2	_	V
Low-level output voltage (BV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	—	0.2	V

 Table 46. Local Bus DC Electrical Characteristics (3.3 V DC)

Note:

1. Note that the symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1.

Table 47 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 2.5 V DC$.

Table 47. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Мах	Unit
Supply voltage 2.5V	BV _{DD}	2.37	2.63	V
High-level input voltage	V _{IH}	1.70	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.7	V
Input current	I _{IH}	_	10	μΑ
$(BV_{IN}^{1} = 0 V \text{ or } BV_{IN} = BV_{DD})$	۱ _{IL}		-15	
High-level output voltage ($BV_{DD} = min, I_{OH} = -1 mA$)	V _{OH}	2.0 BV _{DD} + 0.3		V
Low-level output voltage (BV _{DD} = min, I _{OL} = 1 mA)	V _{OL}	GND – 0.3	0.4	V

Note:

1. The symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1.



Table 49. Local Bus General Timing Parameters (BV_{DD} = 3.3 V DC)—PLL Enabled (continued)

At recommended operating conditions with $\mathsf{BV}_{\mathsf{DD}}$ of 3.3 V ± 5%. (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to LALE assertion	t _{LBKHOV4}	_	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	t _{LBKHOX1}	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	t _{LBKHOX2}	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t _{LBKHOZ1}	_	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ2}	—	2.5	ns	5

Note:

- The symbols used for timing specifications herein follow the pattern of t_{(First two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(First two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- 2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
- 3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
- 7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.
- 8. Guaranteed by design.

Table 50 describes the general timing parameters of the local bus interface at $BV_{DD} = 2.5 \text{ V DC}$.

٦	able 50.	Local I	Bus	s Ger	neral Tir	ning	Parameters	$(\mathbf{BV}_{\mathbf{DD}})$	= 2.5 V DC	C)—PLL Enabled	I

At recommended operating conditions with BV_{DD} of 2.5 V \pm 5%

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	6.67	12	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t _{LBKSKEW}	_	150	ps	7, 8
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	1.9	—	ns	3, 4
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKH2}	1.8	—	ns	3, 4
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	1.1	—	ns	3, 4
LGTA/LUPWAIT input hold from local bus clock	t _{LBIXKH2}	1.1	—	ns	3, 4
LALE output negation to high impedance for LAD/LDP (LATCH hold time)	t _{LBOTOT}	1.5	—	ns	6



Local Bus Controller (eLBC)

Figure 30 through Figure 35 show the local bus signals.

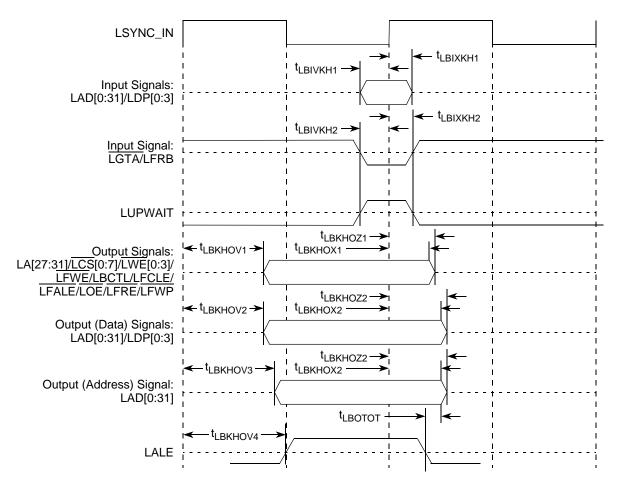


Figure 30. Local Bus Signals, Non-Special Signals Only (PLL Enabled)

Table 52 describes the general timing parameters of the local bus interface at $BV_{DD} = 3.3 \text{ V DC}$ with PLL disabled.

Table 52. Local Bus General Timing Parameters—PLL Bypassed

At recommended operating conditions with BV_{DD} of 3.3 V ± 5%

Parameter	Symbol ¹	Min	Мах	Unit	Notes
Local bus cycle time	t _{LBK}	12	_	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	43	57	%	_
Internal launch/capture clock to LCLK delay	t _{LBKHKT}	2.3	4.0	ns	_
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	5.8	—	ns	4, 5
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKL2}	5.7	_	ns	4, 5
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	-1.3	—	ns	4, 5



Local Bus Controller (eLBC)

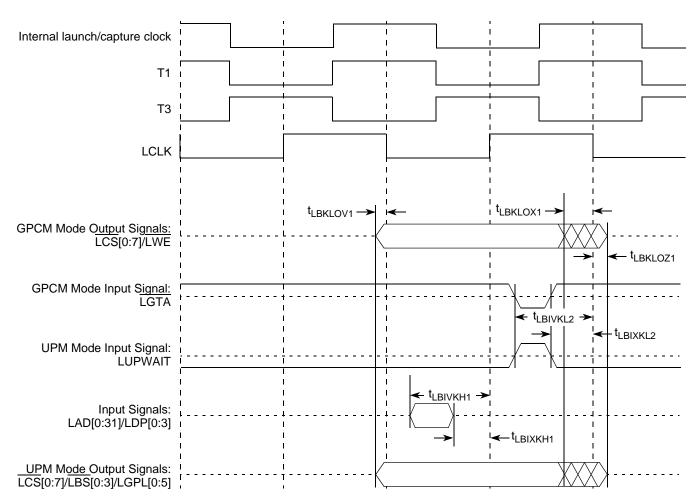


Figure 33. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)



High-Speed Serial Interfaces (HSSI)

Figure 48 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with MPC8572E SerDes reference clock input's DC requirement.

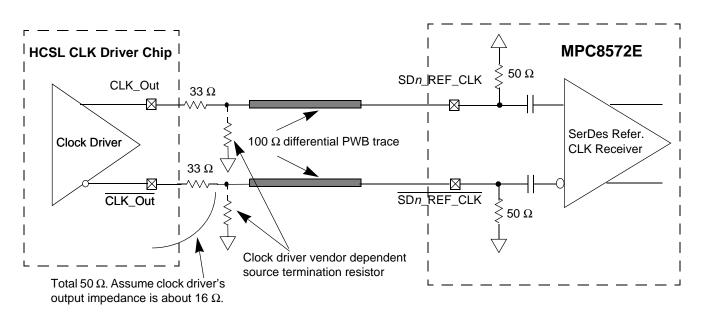
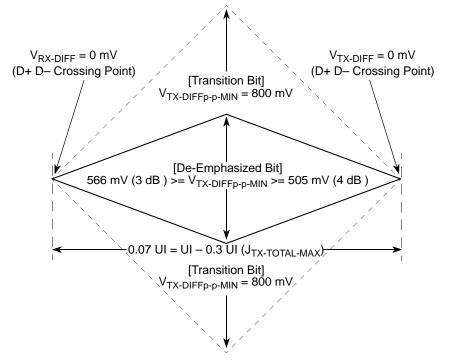


Figure 48. DC-Coupled Differential Connection with HCSL Clock Driver (Reference Only)







16.4.3 Differential Receiver (RX) Input Specifications

Table 63 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Symbol	Parameter	Min	Nominal	Max	Units	Comments
UI	Unit Interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
V _{RX-DIFFp-p}	Differential Input Peak-to-Peak Voltage	0.175	_	1.200	V	$V_{RX-DIFFp-p} = 2^* V_{RX-D+} - V_{RX-D-} $ See Note 2.
T _{RX-EYE}	Minimum Receiver Eye Width	0.4			UI	The maximum interconnect media and Transmitter jitter that can be tolerated by the Receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6 UI.$ See Notes 2 and 3.

Table 63. Differential Receiver (RX) Input Specifications



PCI Express

Symbol	Parameter	Min	Nominal	Max	Units	Comments
T _{RX-EYE-MEDIAN-to-MAX} -JITTER	Maximum time between the jitter median and maximum deviation from the median.		_	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3 and 7.
V _{RX-CM-ACp}	AC Peak Common Mode Input Voltage	_		150	mV	$V_{RX-CM-ACp} = V_{RXD+} + V_{RXD-} /2 - V_{RX-CM-DC} = DC_{(avg)} \text{ of } V_{RX-D+} + V_{RX-D-} /2$ See Note 2
RL _{RX-DIFF}	Differential Return Loss	15		_	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D- lines biased at +300 mV and -300 mV, respectively. See Note 4
RL _{RX-CM}	Common Mode Return Loss	6	_	_	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D- lines biased at 0 V. See Note 4
Z _{RX-DIFF-DC}	DC Differential Input Impedance	80	100	120	Ω	RX DC Differential mode impedance. See Note 5
Z _{RX-DC}	DC Input Impedance	40	50	60	Ω	Required RX D+ as well as D- DC Impedance (50 \pm 20% tolerance). See Notes 2 and 5.
Z _{RX-HIGH-IMP-DC}	Powered Down DC Input Impedance	200 k	_	_	Ω	Required RX D+ as well as D- DC Impedance when the Receiver terminations do not have power. See Note 6.
V _{RX-IDLE} -DET-DIFFp-p	Electrical Idle Detect Threshold	65	_	175	mV	$V_{RX-IDLE-DET-DIFF_{P}} = 2^* V_{RX-D+} - V_{RX-D-} $ Measured at the package pins of the Receiver
T _{RX-IDLE-DET-DIFF-} ENTERTIME	Unexpected Electrical Idle Enter Detect Threshold Integration Time			10	ms	An unexpected Electrical Idle ($V_{RX-DIFFp-p} < V_{RX-IDLE-DET-DIFFp-p}$) must be recognized no longer than $T_{RX-IDLE-DET-DIFF-ENTERING}$ to signal an unexpected idle condition.

Table 63. Differential Receiver (RX) Input Specifications (continued)



Table 66. Short Run Transmitter AC Timing Specifications—2.5 GBaud (continued)

Characteristic	Symbol	Range		Unit	Notes	
Characteristic	Symbol	Min	Мах	Onic	Notes	
Multiple Output skew	S _{MO}	_	1000	-	Skew at the transmitter output between lanes of a multilane link	
Unit Interval	UI	400	400	ps	+/- 100 ppm	

Table 67. Short Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Ra	nge	Unit	Notes
	Symbol	Min	Мах	Onic	NOICS
Output Voltage,	Vo	-0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V _{DIFFPP}	500	1000	mV p-p	—
Deterministic Jitter	J _D	_	0.17	UI p-p	—
Total Jitter	J _T	—	0.35	UI p-p	_
Multiple output skew	S _{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/– 100 ppm

Table 68. Long Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
	Symbol	Min	Мах	Onic	NOLES
Output Voltage,	Vo	-0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V _{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J _D	—	0.17	UI p-p	—
Total Jitter	J _T	—	0.35	UI p-p	—
Multiple output skew	S _{MO}	_	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	+/- 100 ppm



Characteristic	Symbol	Range		Unit	Notes
		Min	Мах	Onic	Notes
Output Voltage,	Vo	-0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V _{DIFFPP}	800	1600	mV p-p	_
Deterministic Jitter	J _D	—	0.17	UI p-p	_
Total Jitter	J _T	—	0.35	UI p-p	_
Multiple output skew	S _{MO}	_	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	400	400	ps	+/- 100 ppm

Table 69. Long Run Transmitter AC Timing Specifications—2.5 GBaud

Table 70. Long Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		l lmit	Notes
	Symbol	Min	Max	Unit	NOLES
Output Voltage,	Vo	-0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V _{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J _D	—	0.17	UI p-p	—
Total Jitter	J _T	—	0.35	UI p-p	—
Multiple output skew	S _{MO}	-	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/- 100 ppm

For each baud rate at which an LP-Serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the transmitter output compliance mask shown in Figure 58 with the parameters specified in Figure 71 when measured at the output pins of the device and the device is driving a 100 Ω +/-5% differential resistive load. The output eye pattern of an LP-Serial transmitter that implements pre-emphasis (to equalize the link and reduce inter-symbol interference) need only comply with the Transmitter Output Compliance Mask when pre-emphasis is disabled or minimized.



Characteristic	Symbol	Range		Unit	Notes
	Symbol	Min	Мах	Onic	NOLES
Differential Input Voltage	V _{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J _D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J _{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance ¹	J _T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S _{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10 ⁻¹²	_	—
Unit Interval	UI	800	800	ps	+/– 100 ppm

Table 72. Receiver AC Timing Specifications—1.25 GBaud

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 59. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

Characteristic	Symbol	Range		llait	Notes	
		Min	Мах	Unit	NOLES	
Differential Input Voltage	V _{IN}	200	1600	mV p-p	Measured at receiver	
Deterministic Jitter Tolerance	J _D	0.37	—	UI p-p	Measured at receiver	
Combined Deterministic and Random Jitter Tolerance	J _{DR}	0.55	—	UI p-p	Measured at receiver	
Total Jitter Tolerance ¹	J _T	0.65	—	UI p-p	Measured at receiver	
Multiple Input Skew	S _{MI}	_	24	ns	Skew at the receiver input between lanes of a multilane link	
Bit Error Rate	BER	—	10 ⁻¹²	—	—	
Unit Interval	UI	400	400	ps	+/– 100 ppm	

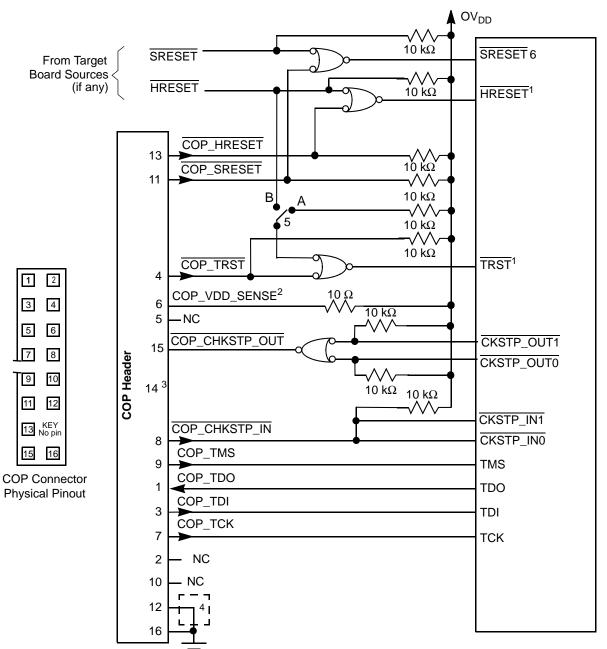
Table 73. Receiver AC Timing Specifications—2.5 GBaud

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 59. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.



System Design Information



Notes:

- 1. The COP port and target board should be able to independently assert HRESET and TRST to the processor to fully control the processor as shown here.
- 2. Populate this with a 10 Ω resistor for short-circuit/current-limiting protection.
- 3. The KEY location (pin 14) is not physically present on the COP header.
- 4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
- 5. This switch is included as a precaution for BSDL testing. The switch should be closed to position A during BSDL testing to avoid accidentally asserting the TRST line. If BSDL testing is not being performed, this switch should be closed to position B.
- 6. Asserting SRESET causes a machine check interrupt to the e500 cores.